# **InterFET** HYBRID TECHNOLOGY

#### **Features**

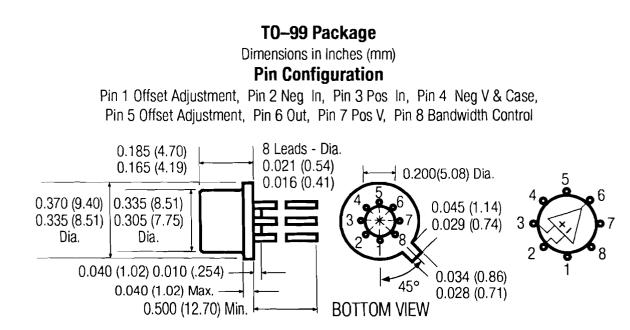
- - 55°C to + 200°C Specifications
- 300nA Max Input Bias Current at + 200°C
- ± 6 mV Max Input Offset Voltage at + 200°C
- ± 5 µV/°C Typical Input Offset Voltage Coefficient
- 12 MHz Bandwidth Typical
- Hermetic Package with Standard Pinout (741) Type
- Pin Compatible with Burr Brown OPA11HT

# Description

The I-6H001 is a wide-temperature range, general purpose, operational amplifier ideally suited for 200°C applications. Model I-6H001 is internally compensated for stability at all gains. Pins are available for special tailoring of the bandwidth compensation. Inputs are protected against common-mode voltages up to the value of the power supplied, while the output is current limited to offer short-circuited protection. TO-99 hermetic package has standard 741-type pinout arrangement.

# **Absolute Maximum Ratings**

Supply Voltage	± 22 V
Differential Input Voltage	± 12 V
Operating Temperature Range – 55°C to	+ 200°C
Storange Temperature Range – 65°C to	+ 250°C
Lead Temperature (soldering, 10 sec)	+ 300°C
Output Short-Circuit Duration	
Continuous Junction Temperature	+250°C





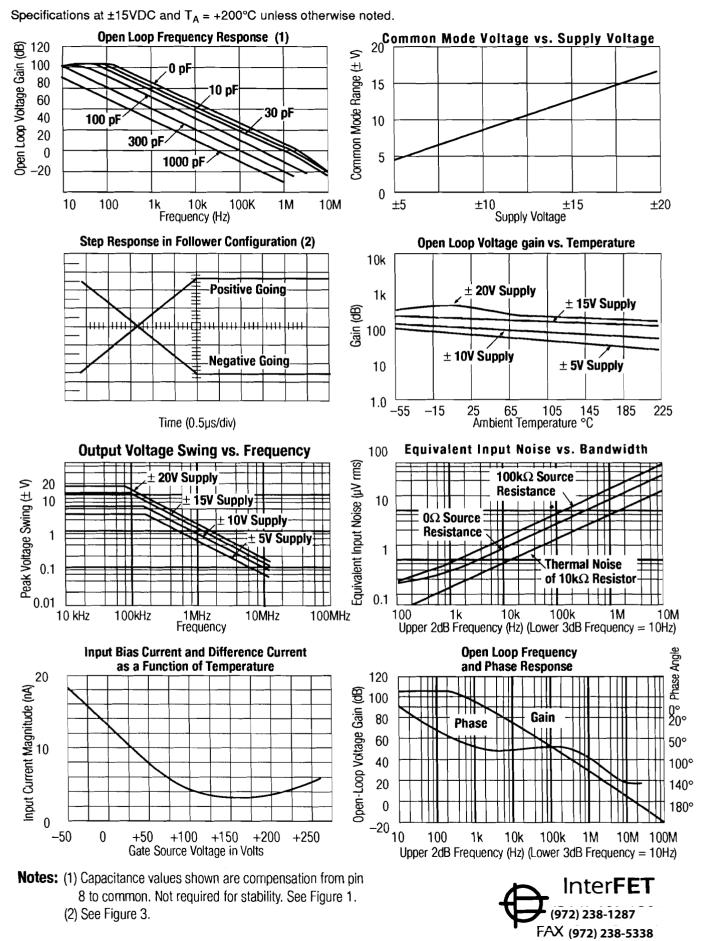
InterFET	HYBRID	TECHNOL	OGY

1-6H001

ecifications at $\pm 15$ VDC and $T_A = +200$ °C unless otherwise	noted.	Min	Тур	Max	Unit
PEN LOOP GAIN	- <u>-</u>				
DC, single-ended	Av				
No Load			103		dB
$R_{\perp} = 2k\Omega$		94	100		dB
RATED OUTPUT					
Voltatge: $R_L = 2k\Omega$	V <sub>OM</sub>	± 10	<u>± 12</u>		V
Current: $(T_A = 25^{\circ}C)$	ом	<u>±15</u>	<u>± 23</u>		mA
DYNAMIC RESPONSE ( $T_A = 25^{\circ}C$ )					
Small-Signal Bandwidth (OdB)		12	· · · · · · · · · · · · · · · · · · ·		<u>M</u> H
Full-Power Bandwidth V out = $\pm 10V$	BWfp	50	75		<u>kH</u> z
Slew Rate $RL = 2K\Omega$	SR	± 4	± 7		V/µs
Settling Time: (0.1%)			1.5		μs
Rise Time (10% to 90%, small signal)			30		ns
NPUT OFFSET VOLTAGE					
Initial (without adj. at 25°C)	V <sub>10</sub>		± 2	± 5	mV
Over Temperature ( $T_A = + 200^{\circ}C$ )				± 6	mV
Over Temperature ( $T_A = -55^{\circ}C$ )				± 7	mV
Average V <sub>IO</sub> Coefficient			± 5		μV/°C
Average $V_{10}$ Coefficient vs. Supply Voltage (T <sub>A</sub> =	= 25°C)		± 10	± 200	μV/V
INPUT BIAS CURRENT			I	I	
Initial at + 25°C			± 10		nA
Over Temperature ( $T_A = + 200^{\circ}C$ )				± 300	nA
Over Temperature ( $T_A = -55^{\circ}C$ )				± 40	nA
Average I <sub>IB</sub> Coefficient			± 0.1		nA/°(
<b>INPUT IMPEDANCE</b> $(T_A = 25^{\circ}C)$	J		<u> </u>	·	
Differential	$\overline{r_1}$	100	300		MΩ
Differential	C <sub>1</sub>		3		pF
Common Mode	r <sub>1</sub> (CM)		1000		ΜΩ
Common Mode	$C_1$ (CM)		3		pF
INPUT VOLTAGE RANGE					
Common Mode	1		1	± 11	V
Differential Mode				± 12	v
Common Mode Rejection CMR	80	100		dB	•
<u>Over_Temperature (- 55°C <math>\leq</math> T<sub>A</sub> <math>\leq</math> + 200°C)</u>	00	100	+		
<b>POWER SUPPLY</b> ( $T_A = 25^{\circ}$ C)		<b>-</b>	<b></b>		
Rated Voltage	V	<u> </u>	1	± 15	v
	V <sub>cc</sub>		. <u>0 to 10</u>		v
Voltage Range, Derated			$\pm 8 \text{ to } \pm 22$	T	
Current, Quiescent	I <sub>0</sub>		± 3	± 4.5	mA
Over Temperature (- $55^{\circ}C \le T_A \le + 200^{\circ}C$ )					
Power Supply Rejection ( $T_A = 200^{\circ}C$ )	P <sub>SRR</sub>	80	100		dB
TEMPERATURE RANGE		i ————	+ <u> </u>		<u>+</u>
Operating			- 55	+ 200	0°
Storage			55	+ 200	<u>0°</u>



InterFET HYBRID TECHNOLOGY



# 1-6H001 InterFET HYBRID TECHNOLOGY

# **Applications**

#### **Bandwidth Compensation**

The frequency response of the I-6H001 can be adjusted by use of an external compensation capacitor from pin 8 to common as show in Figure 1. The open-loop frequency response curves illustrate the effect of various values of capacitance. The I-6H001 is stable at any gain level without the use of compensation, provided that stray wiring capacitance and/or load capacitance are not excessive, and that moderate values of feedback resistance are used ( $R_{FB} \leq 10 \text{ k}\Omega$ ). A load capacitance of 50pF is desirable in all feed back configurations.

#### Stability

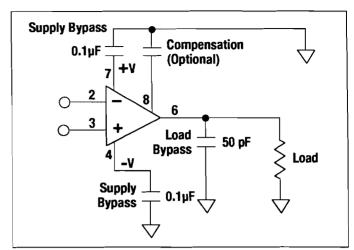
Because the I-6H001 is an extremely fast amplifier with high gain, stray wiring capacitance and inductance in power supply leads can cause circuit oscillation. This can be prevented by proper circuit layout (all leads or patterns as short as possible) and properly bypassing the power supply line to common at points close to the amplifier. In addition, it is recommended the the load be bypassed by a 50pF capacitor. See Figure 1.

#### **Offset Voltage and Adjustment**

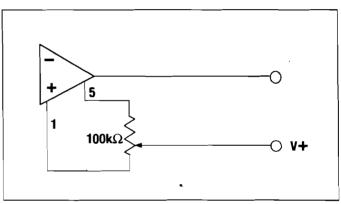
Although the offset voltage of these amplifiers is only a few millivolts, it may in some cases be desirable to null this offset. This is done by use of a  $100k\Omega$  potentiometer as shown in Figure 2.

#### Test Circuit–Dynamic Response

The test circuit of Figure 3 is used for measurement of slew rate, settling time, rise time and overshoot. Both rise time and overshoot are measured for a small output signal ( $V_{OUT} = \pm 100$ mV). Slew rate and settling time are measured by a 10V, peak-to-peak, square wave.









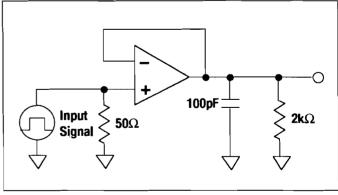


Figure 3

